

L Number	Hits	Sear h Text	DB	Time stamp
-	63	(vertical near pillar).clm. and base.clm. wall.clm. and (memory or storage).clm. and transistor.clm. and vertical.ab. and pillar.ab. and "257" and layer.clm. and (insulation or insulating or dielectric or oxide).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:33
-	63	(vertical near pillar).clm. and base.clm. wall.clm. and (memory or storage).clm. and transistor.clm. and vertical.ab. and pillar.ab. and layer.clm. and (insulation or insulating or dielectric or oxide).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:33
-	63	(vertical near pillar).clm. and base.clm. wall.clm. and (memory or storage).clm. and transistor.clm. and vertical.ab. and pillar.ab. and layer.clm. and (insulation or insulating or dielectric or oxide).clm. and semiconductor.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:33
-	0	(vertical near pillar).clm. and base.clm. and wall.clm. and (memory or storage).clm. and transistor.clm. and vertical.ab. and pillar.ab. and layer.clm. and (insulation or insulating or dielectric or oxide).clm. and semiconductor.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:34
-	0	(vertical near pillar).clm. and base.clm. and wall.clm. and (memory or storage).clm. and transistor.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:34
-	34	(vertical near pillar).clm. and (memory or storage).clm. and transistor.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:34
-	20	(vertical near pillar).clm. and (memory or storage).clm. and transistor.clm. and (vertical near pillar).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:36
-	17	(vertical near pillar).clm. and (memory or storage).clm. and transistor.clm. and (vertical near pillar).ab. and layer.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:36
-	17	(vertical near pillar).clm. and (memory or storage).clm. and transistor.clm. and (vertical near pillar).ab. and layer.clm. and (insulating or insulation or dielectric or oxide).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:36

-	0	(vertical near pillar). clm. and (memory or storage).clm. and transistor.clm. and (vertical near pillar).ab. and layer.clm. and (insulating or insulation or dielectric or oxide).clm. and wall. lm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:36
-	0	(vertical near pillar).clm. and (memory or storage).clm. and transistor.clm. and (vertical near pillar).ab. and layer.clm. and (insulating or insulation or dielectric or oxide).clm. and core.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:37
-	2	(vertical near pillar).clm. and core.clm. and (transistor or storage or memory).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:37
-	1	(vertical near pillar).clm. and (statistical near mask).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:38
-	1	(vertical near pillar).clm. and (statistical near mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:38
-	11	(vertical near pillar).clm. and (mask).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:56
-	3	(vertical near pillar).clm. and (mask).ti,ab,clm. and (vertical near pillar).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:56
-	6	(vertical near pillar).clm. and (mask).ti,ab,clm. and (vertical).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:57
-	265	(vertical).ab. and (memory or storage or transistor).ab. and (memory or storage or transistor).clm. and vertical.clm. and mask.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:57
-	227	(vertical).ab. and (memory or storage or transistor).ab. and (memory or storage or transistor).clm. and vertical.clm. and mask.ti,ab,clm. and layer.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:58

	205	(vertical).ab. and (memory or storage or transistor).ab. and (memory storage or transistor).clm. and vertical.clm. and mask. lm. and lay r.clm.	USPAT; U -P PUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:58
	47	(vertical).ab. and (memory or storage or transistor).ab. and (memory or storage or transistor).clm. and vertical.clm. and mask.clm. and layer.clm. and (vertical near (semiconductor or pillar or transistor or memory or storage)).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:58
	25	(vertical).ab. and (memory or storage or transistor).ab. and (memory or storage or transistor).clm. and vertical.clm. and mask.clm. and layer.clm. and (vertical near (semiconductor or pillar or transistor or memory or storage)).clm. and (vertical near (semiconductor or pillar or transistor or memory or storage)).ab.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 10:59
	1	(vertical).ab. and (memory or storage or transistor).ab. and (memory or storage or transistor).clm. and vertical.clm. and mask.clm. and layer.clm. and (vertical near (semiconductor or pillar or transistor or memory or storage)).clm. and (vertical near (semiconductor or pillar or transistor or memory or storage)).ab. and (mask near10 (statistics or statistically or statistical))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/10/27 11:00